ABSTRACT

There is provided is a technique including: a process chamber configured to process a substrate; a first gas supplier configured to supply a metal-containing gas into the process chamber; a second gas supplier configured to supply a first oxygen-containing gas ~~from an interior of~~into the process chamber; and an exhauster including a gas exhaust pipe and a trap configured to collect a component of the metal-containing gas contained in an exhaust gas by using plasma, the exhauster being configured to discharge ~~an~~the exhaust gas ~~containing a component of the metal-containing gas~~ from ~~the~~an interior of the process chamber~~, wherein the exhauster includes a gas exhaust pipe, a pump configured to exhaust the interior of the process chamber, an auxiliary pump configured to support the pump, and a trap disposed between the pump and the auxiliary pump and configured to collect the component of the metal-containing gas by using plasma~~.